

# Maximum Ratings (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	100	V
Gate-Source Voltage			V <sub>GSS</sub>	±16	V
Continuous Durin Comment (Nata 5) // 40)/	(Note 6)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	2.24 1.79	А
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	(Note 5)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	1.87 1.50	А
Maximum Continuous Body Diode Forward Current (Note 6)			Is	1.50	Α
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I <sub>DM</sub>	6.60	А

### Thermal Characteristics (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Dawer Discinction (Note 6)	$T_A = +25^{\circ}C$	6	1.67	W	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +70°C	$P_{D}$	1.07	VV	
Thermal Resistance, Junction to Ambient	(Note 6)	D	75	°C/W	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	108		
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C	

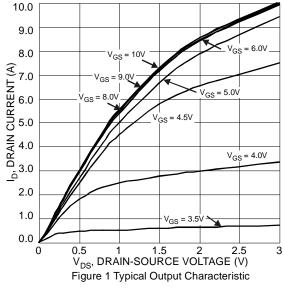
# Electrical Characteristics (@T<sub>A</sub> = +25°C unless otherwise specified.)

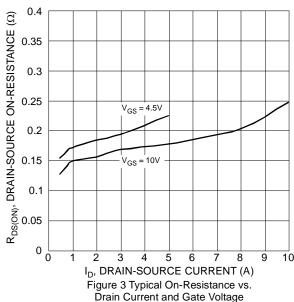
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)						•	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 100V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(th)}$	1	1.8	2.5	٧	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	172	220	mΩ	$V_{GS} = 10V, I_D = 1.6A$	
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)		211	250		$V_{GS} = 4.5V, I_D = 1.3A$	
Diode Forward Voltage	$V_{SD}$	_	0.77	1.2	V	$V_{GS} = 0V, I_{S} = 1.1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	_	401	_		$V_{DS} = 25V$ , $V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss	_	22		pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	17	_			
Gate Resistance	$R_g$	_	2.1	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	4.1	_		V <sub>DS</sub> = 50V, I <sub>D</sub> = 1.6A	
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_g$	_	8.3	_	nC		
Gate-Source Charge	$Q_{gs}$	_	1.5	_	IIC		
Gate-Drain Charge	$Q_{gd}$	_	2	_			
Turn-On Delay Time	t <sub>D(on)</sub>	_	6.8	_		$V_{DS} = 50V, V_{GS} = 4.5V,$ $R_{G} = 6.8\Omega, I_{D} = 1A$	
Turn-On Rise Time	t <sub>r</sub>	_	8.2	_			
Turn-Off Delay Time	t <sub>D(off)</sub>	_	7.9	_	ns		
Turn-Off Fall Time	t <sub>f</sub>	_	3.6	_			
Reverse Recovery Time	t <sub>rr</sub>	_	17	_	ns	1 4 4 0 4 1/4 4 4000 / 1 5	
Reverse Recovery Charge	Q <sub>rr</sub>	_	9.8	_	nC	I <sub>F</sub> = 1.1A, di/dt =100A/μs	

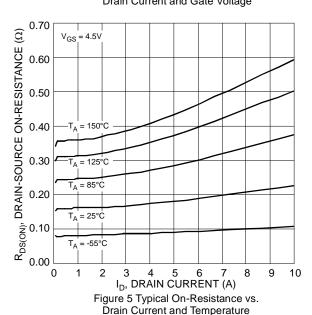
Notes:

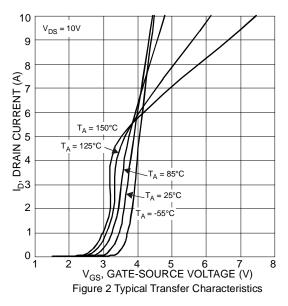
- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate.
- 7 .Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.

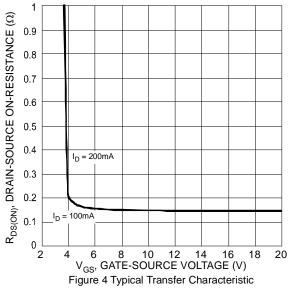












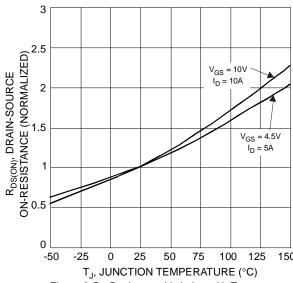
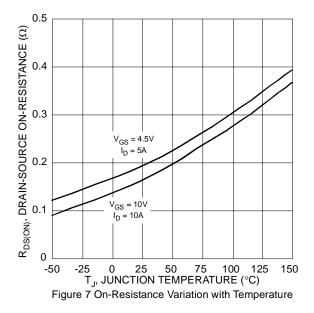


Figure 6 On-Resistance Variation with Temperature





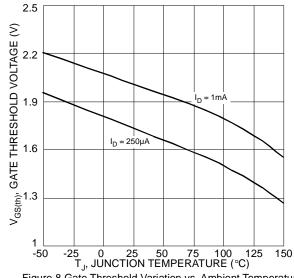
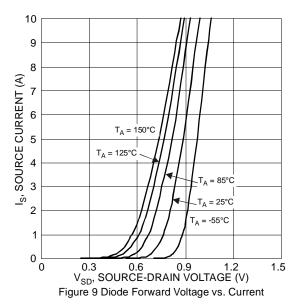
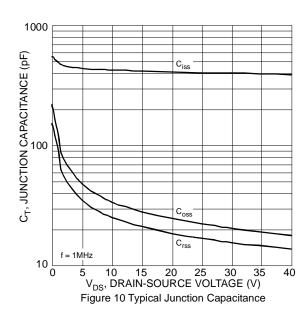
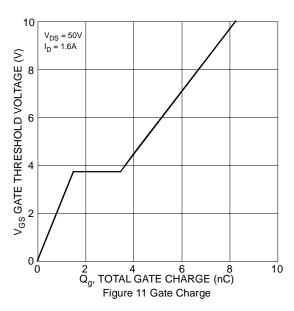
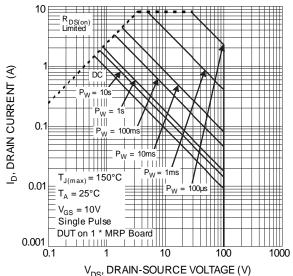


Figure 8 Gate Threshold Variation vs. Ambient Temperature



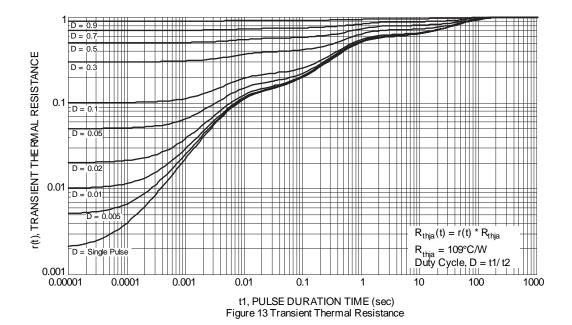






 $\rm V_{\rm DS}$ , DRAIN-SOURCE VOLTAGE (V) Figure 12 SOA, Safe Operation Area

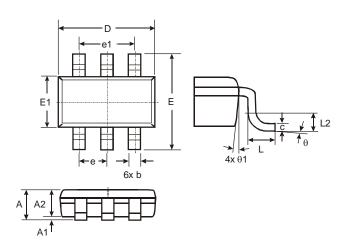






### **Package Outline Dimensions**

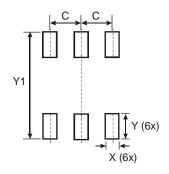
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	TSOT26					
Dim	Min	Max	Тур			
Α		1.00	_			
<b>A</b> 1	0.01	0.10				
A2	0.84	0.90				
D			2.90			
E			2.80			
E1			1.60			
b	0.30	0.45	_			
С	0.12	0.20	_			
е			0.95			
e1			1.90			
L	0.30	0.50				
L2			0.25			
θ	0°	8°	4°			
θ1	4°	12°	_			
All D	All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.950
X	0.700
Y	1.000
Y1	3.199



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